



Contribution ID: 169

Type: **Poster**

## Calculation of activation temperature of TiZrV getter film

*Wednesday 20 June 2018 18:00 (20 minutes)*

TiZrV film should be baked to make oxygen atom diffuse from the surface passivation layer into the interior of the film. Oxygen diffusion along grain boundary plays dominant role during activation. This process was simulated and the relation between activation temperature and grain size was obtained.

**Author:** Dr ZHANG, Bo (University of Science and Technology of China)

**Co-authors:** WANG, Yong (University of Science and Technology of China); WANG, Sihui (University of Science and Technology of China)

**Presenter:** Dr ZHANG, Bo (University of Science and Technology of China)

**Session Classification:** Poster Session Wednesday

**Track Classification:** Thin Film & Surface Engineering